

CLAIMS

1. A ceramic substrate comprising a conductive layer disposed internally or on the surface thereof, wherein said ceramic substrate comprises a nitride ceramic and boron is contained in said nitride ceramic.

2. The ceramic substrate according to Claim 1, wherein the boron content of said nitride ceramic is 0.01 to 50 ppm.

3. The ceramic substrate according to Claim 1, wherein oxygen is further contained in said ceramic substrate.

4. A sintered aluminum nitride body which contains boron.

5. The sintered aluminum nitride body according to Claim 4, wherein the boron content of said sintered aluminum nitride body is 0.01 to 50 ppm.

6. The sintered aluminum nitride body according to Claim 4, wherein oxygen is further contained in said ceramic substrate.